



DMP3004SSS

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	4.0mΩ @ V _{GS} = -10V	-16.2A
-30V	6.5mΩ @ V _{GS} = -4.5V	-12.8A

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

P-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

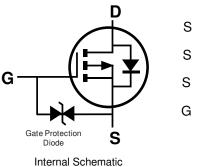
Mechanical Data

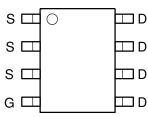
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram Below
- Terminals: Finish—Matte Tin Annealed Over Copper Lead Frame.
 Solderable per MIL-STD-202, Method 208 (21)
- Weight: 0.074 grams (Approximate)





Top View





Top View Pin Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3004SSS-13	SO-8	2500/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

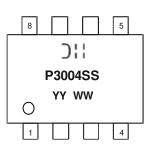
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, see https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 6)	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		-16.2 -13.0	
	t < 10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-23.4 -18.7	A
Maximum Continuous Body Diode Forward Current (Note 6)			ls	-1.8	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-110	A
Avalanche Current, L=0.1mH (Note 7)			I _{AS}	-44	А
Avalanche Energy, L=0.1mH (Note 7)			E _{AS}	98	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1.2	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Devi	103	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	R _{eja}	50	-C/W	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	PD	1.6	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	79	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t < 10s	R _{eja}	38	°C/W	
Thermal Resistance, Junction to Case (Note 6)		R _{eJC}	11	°C/W	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C	

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	-,		- 76				
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	$V_{GS} = 0V, I_D = -250 \mu A$	
Zero Gate Voltage Drain Current	IDSS	_	—	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	—	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)			•	•	•		
Gate Threshold Voltage	V _{GS(TH)}	-1.0	—	-2.5	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance	Р	_	3.2	4.0	mΩ	$V_{GS} = -10V, I_D = -20A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	—	5.2	6.5	11152	$V_{GS} = -4.5V, I_D = -15A$	
Diode Forward Voltage	V _{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	7693	—	pF		
Output Capacitance	Coss	—	1426	—	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	—	966	_	pF		
Gate Resistance	R _g	—	5.4	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	—	73	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	156	—	nC		
Gate-Source Charge	Q _{gs}	_	23	—	nC	$V_{DS} = -15V, I_D = -20A$	
Gate-Drain Charge	Q _{gd}	_	34	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	8.3	—	ns		
Turn-On Rise Time	t _R	_	6.8	—	ns	V _{DD} = -15V, V _{GS} = -10V,	
Turn-Off Delay Time	t _{D(OFF)}	_	267	_	ns	$R_g = 1\Omega, I_D = -20A$	
Turn-Off Fall Time	tF	_	223	_	ns		
Reverse Recovery Time	t _{RR}	_	31	—	ns		
Reverse Recovery Charge	Q _{RR}	_	25	_	nC	- I _F = -10A, dI/dt = 100A/μs	

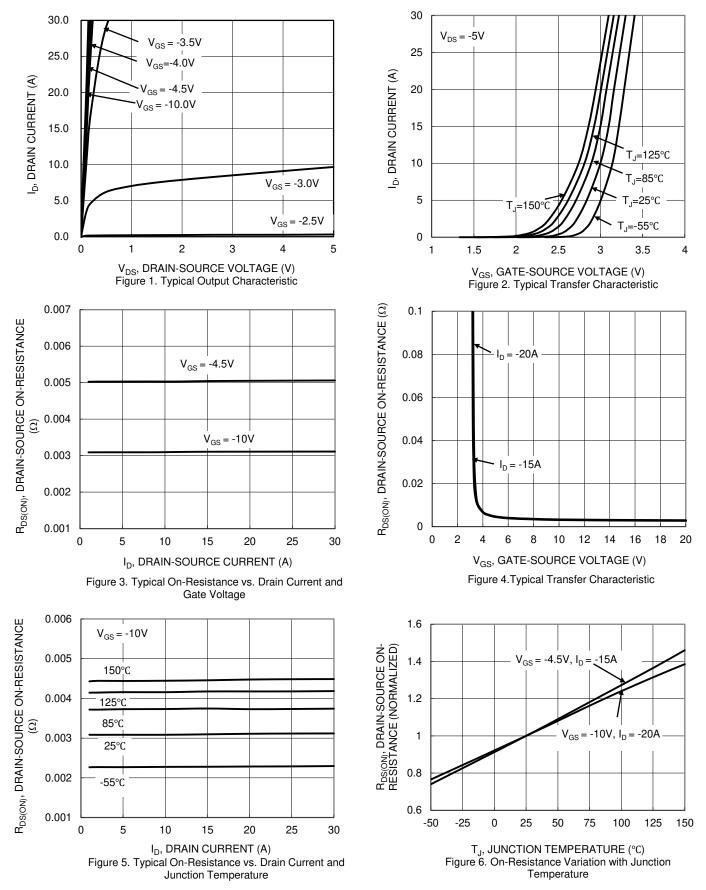
Notes:

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Coverstand by device. The option of the product testing.

9. Guaranteed by design. Not subject to product testing.



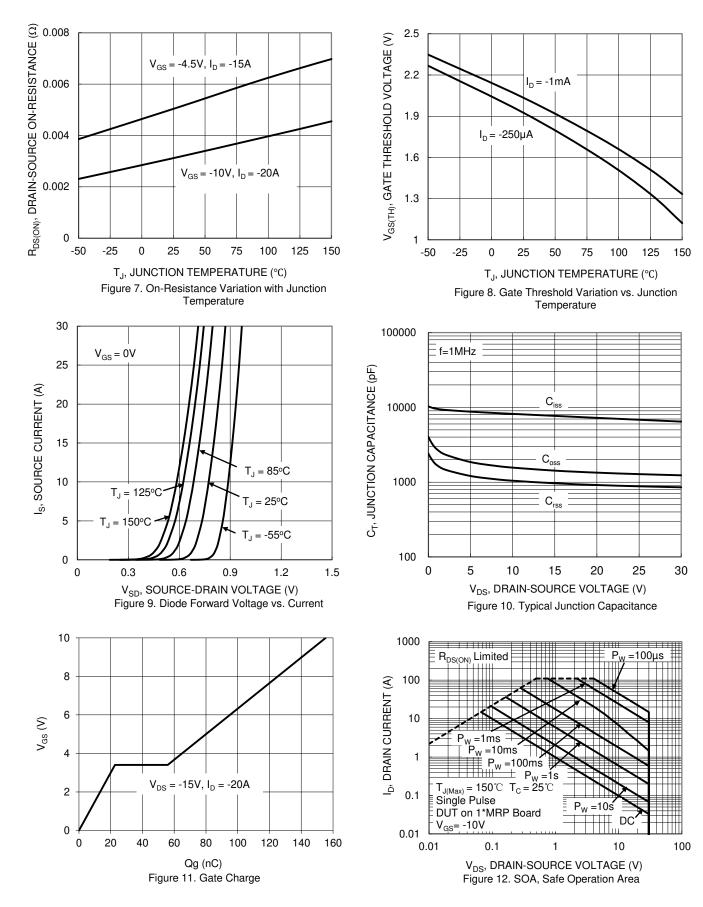
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DMP3004SSS Document number: DS39071 Rev. 3 - 2

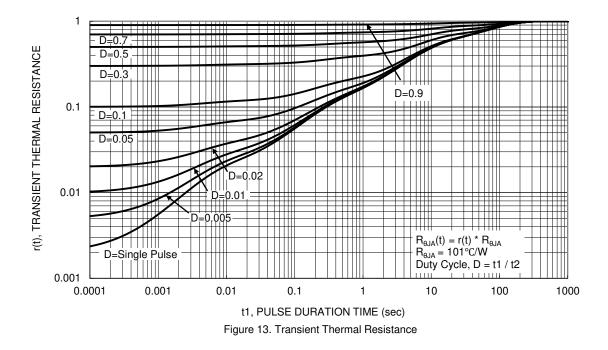


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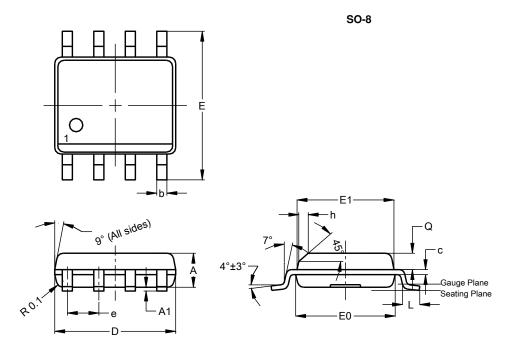






Package Outline Dimensions

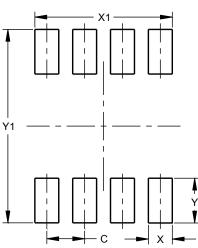
Please see http://www.diodes.com/package-outlines.html for the latest version.



SO-8						
Dim	Min	Max	Тур			
Α	1.40	1.50	1.45			
A1	0.10	0.20	0.15			
b	0.30	0.50	0.40			
С	0.15	0.25	0.20			
D	4.85	4.95	4.90			
Е	5.90	6.10	6.00			
E1	3.80	3.90	3.85			
E0	3.85	3.95	3.90			
е			1.27			
h	-		0.35			
L	0.62	0.82	0.72			
Q	0.60	0.70	0.65			
All	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SO-8

Dimensions	Value (in mm)			
С	1.27			
Х	0.802			
X1	4.612			
Y	1.505			
Y1	6.50			



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